# Jonathan Pelz

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/436024/publications.pdf

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| 19 | 362 | 1040056<br>9 | 1058476<br>14 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 19 | 19 | 19 | 375 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Local trap spectroscopy on cross-sectioned AlGaN/GaN devices with <i>in situ</i> biasing. Applied Physics Letters, 2019, 114, . | 3.3 | 2 |
| 2 | Correlative Defect Characterization in Semiconductors via Electron Channeling Contrast Imaging and Scanning Deep Level Transient Spectroscopy. Microscopy and Microanalysis, 2018, 24, 1056-1057. | 0.4 | 0 |
| 3 | Spatial correlation of the EC-0.57 eV trap state with edge dislocations in epitaxial n-type gallium nitride. Journal of Applied Physics, 2018, 123, . | 2.5 | 11 |
| 4 | Direct nm-scale spatial mapping of traps in CIGS. , 2015, , . |  | 0 |
| 5 | Direct nm-Scale Spatial Mapping of Traps in CIGS. IEEE Journal of Photovoltaics, 2015, 5, 1482-1486. | 2.5 | 32 |
| 6 | Correlation of electrical spin injection and non-linear charge-transport in Fe/MgO/Si. Applied Physics Letters, 2013, 103, . | 3.3 | 17 |
| 7 | Spatially-resolved spectroscopic measurements of <i>Ec</i>â€‰âˆ’â€‰0.57â€‰eV traps in AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2013, 102, . | 3.3 | 91 |
| 8 | Nm-scale measurements of fast surface potential transients in an AlGaN/GaN high electron mobility transistor. Applied Physics Letters, 2012, 100, . | 3.3 | 31 |
| 9 | Nanoscale Characterization of Metal/Semiconductor Nanocontacts. AIP Conference Proceedings, 2005, , . | 0.4 | 0 |
| 10 | Calculated potential profile near charged threading dislocations at metal/semiconductor interfaces. Journal of Applied Physics, 2002, 92, 6010-6013. | 2.5 | 6 |
| 11 | Relaxed InAsP layers grown on step graded InAsP buffers by solid source MBE. Materials Research Society Symposia Proceedings, 2002, 722, 1021. | 0.1 | 4 |
| 12 | OBSERVATION OF DIRECT-CURRENT-INDUCED STEP BENDING PATTERNS ON Si(001). Surface Review and Letters, 2000, 07, 577-582. | 1.1 | 3 |
| 13 | Ultrahigh vacuum dual fluid line rotatable connector. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 674-675. | 2.1 | 0 |
| 14 | Nanometer-scale investigation of metal-SiC interfaces using ballistic electron emission microscopy. Journal of Electronic Materials, 1998, 27, 345-352. | 2.2 | 19 |
| 15 | Investigation of ultrathin SiO[sub 2] film thickness variations by ballistic electron emission microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2302. | 1.6 | 9 |
| 16 | Ballistic-electron emission microscopy studies of charge trapping in SiO2. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2864. | 1.6 | 42 |
| 17 | Evolution of atomicâ€scale roughening on Si(001)â€(2Ã—1) surfaces resulting from high temperature oxidation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 772-776. | 2.1 | 54 |
| 18 | Elevated temperature oxidation and etching of the Si(111) 7Ã—7 surface observed with scanning tunneling microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1649-1653. | 2.1 | 41 |

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|---|---|---|---|
| 19 | Alignment of Adsorbate-Induced Defects on Silicon(001) 2Ã—1 Observed with STM. Materials Research Society Symposia Proceedings, 1993, 318, 25. | 0.1 | 0 |